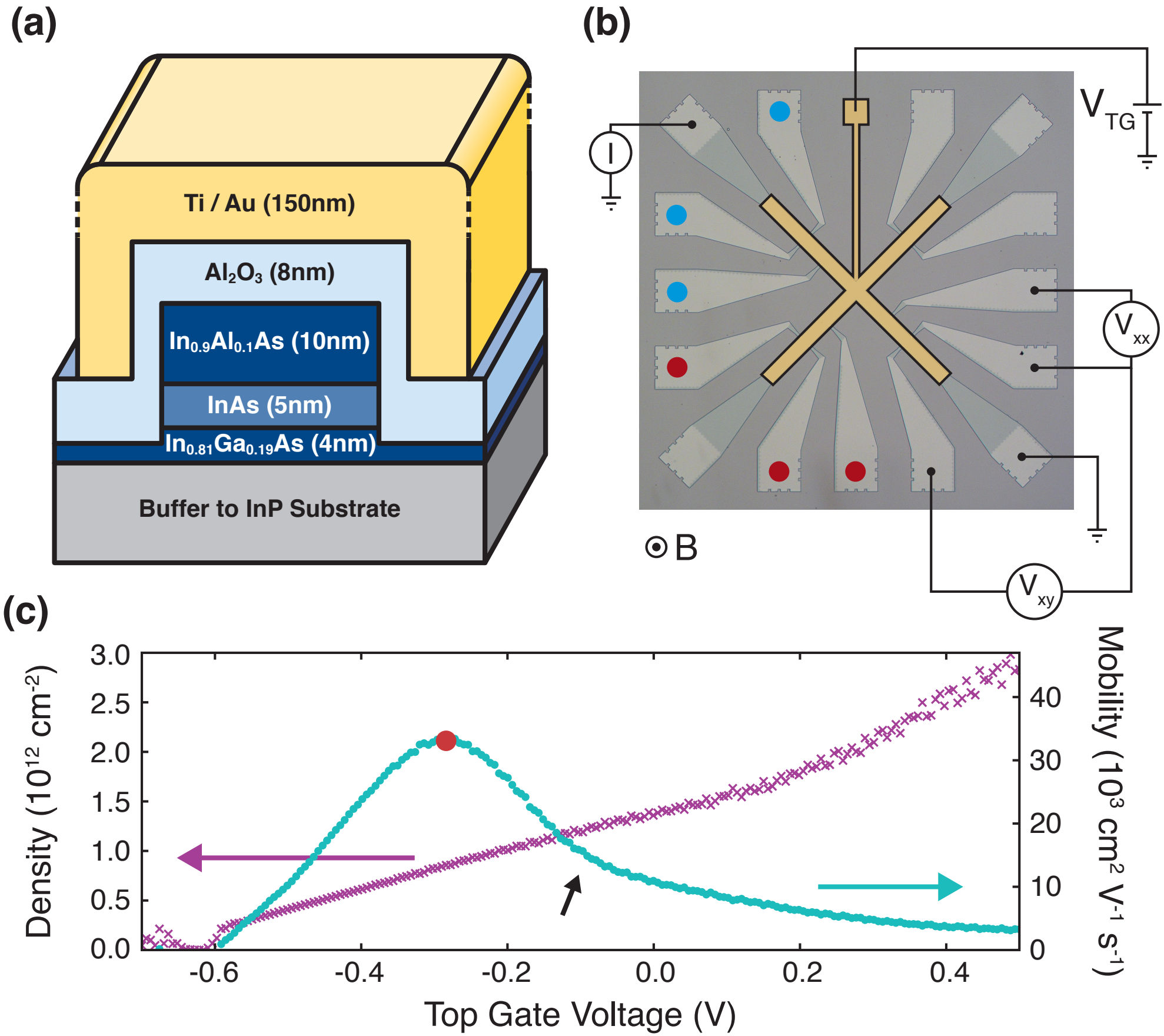
(a)
Ti / Au (150nm)
Al2O3 (8nm)
In0.9Al0.1As (10nm)
InAs (5nm)
In0.81Ga0.19As (4nm)
Buffer to InP Substrate
(b)
I
VTG
Vxx
Vxy
B
(c)
Density (10^12 cm^-2)
Mobility (10^3 cm^2 V^-1 s^-1)
Top Gate Voltage (V)
3.0
2.5
2.0
1.5
1.0
0.5
0.0
40
30
20
10
0
-0.6
-0.4
-0.2
0.0
0.2
0.4